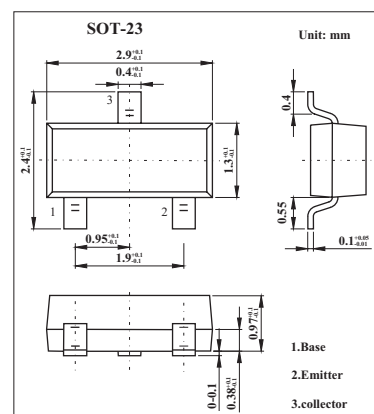


Epitaxial Planar PNP Silicon Transistor

2SA1455K

■ Features

- High breakdown voltage: $V_{CE0} = -120V$
- Low noise design: $NF = 0.2dB$ (Typ.)

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-120	V
Collector-emitter voltage	V_{CEO}	-120	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-50	mA
Collector power dissipation	P_C	200	mW
Junction temperature	T_J	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV_{CBO}	$I_C = -50\mu A$	-120			V
Collector-emitter breakdown voltage	BV_{CEO}	$I_C = -1mA$	-120			V
Emitter-base breakdown voltage	BV_{EBO}	$I_E = -50\mu A$	-5			V
Collector cutoff current	I_{CBO}	$V_{CB} = -100V$			-0.5	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -4V$			-0.5	μA
DC current transfer ratio	h_{FE}	$V_{CE} = -6V, I_C = -2mA$	180		820	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10mA, I_E = -1mA$			-0.5	V
Output capacitance	f_T	$V_{CE} = -12V, I_E = 2mA, f = 30MHz$		140		MHz
Transition frequency	C_{ob}	$V_{CB} = -12V, I_E = 0A, f = 1MHz$		3.2		pF

■ h_{FE} Classification

Marking	G		
Rank	R	S	E
h_{FE}	180~390	270~560	390~820